Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT78 plastic package. The "series ET" triac balances the requirements of commutation performance and gate sensitivity. The "sensitive gate" "series ET" is intended for interfacing with low power drivers including microcontrollers where "high junction operating temperature" capability is required.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- · High commutation capability with sensitive gate
- High junction operating temperature capability
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- · Applications subject to high temperature
- · Electronic thermostats (heating and cooling)
- · High power motor controls e.g. washing machines and vacuum cleaners
- · Refrigeration and air-conditioner compressor controls

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage			-	-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 126 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3		-	-	16	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5		-	-	140	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$		-	-	150	Α
T _j	junction temperature			-	-	150	°C
Static characteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$		2	-	10	mA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	2	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	20	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	0.8	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 10 V/ μ s; gate open circuit	1.2	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 1 V/ μ s; gate open circuit	6	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2——T1
2	T2	main terminal 2	├	G sym051
3	G	gate		Symost
mb	T2	mounting base; main terminal 2	1 2 3	
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Table 6. Ordering information							
Type number	Package						
	Name	Description	Version				
BTA316-600ET	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				
BTA316-600ET/DG	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

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7. Marking

Table 4. Marking codes

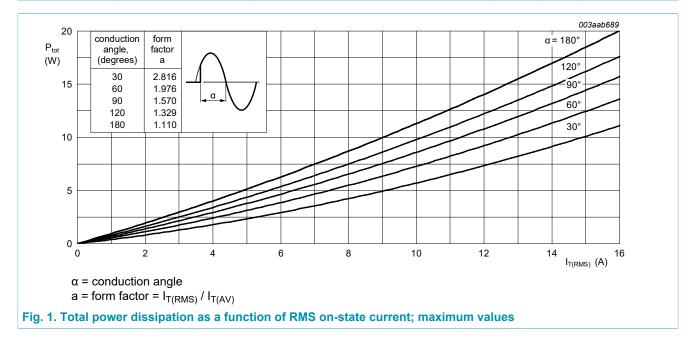
Type number	Marking code
BTA316-600ET	
BTA316-600ET/DG	BTA316-600ETDG

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 126 ^{\circ}\text{C}$; $\overline{\text{Fig. 1}}$; Fig. 2; Fig. 3	-	16	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	140	Α
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	150	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	98	A²s
dl _T /dt	rate of rise of on-state current	I _G = 0.2 A	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C



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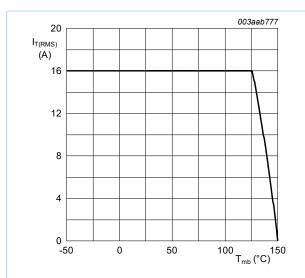
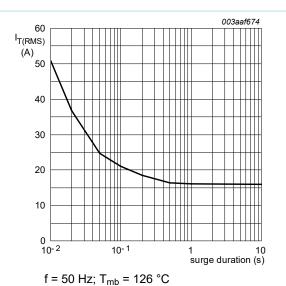


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



2 PMS on otata assument as a functi

Fig. 3. RMS on-state current as a function of surge duration; maximum values

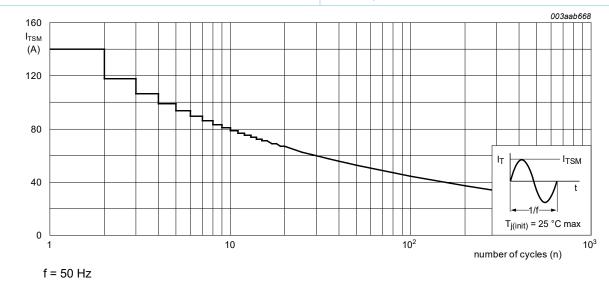
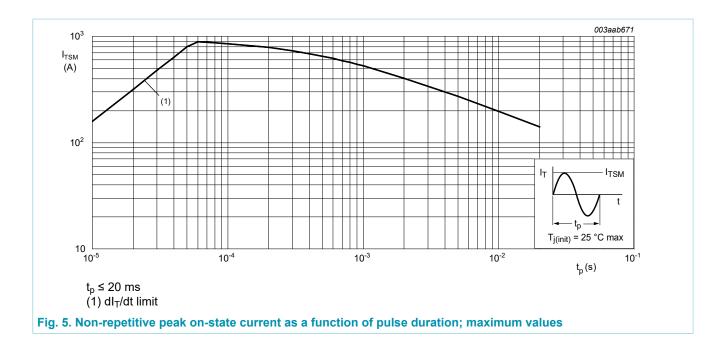


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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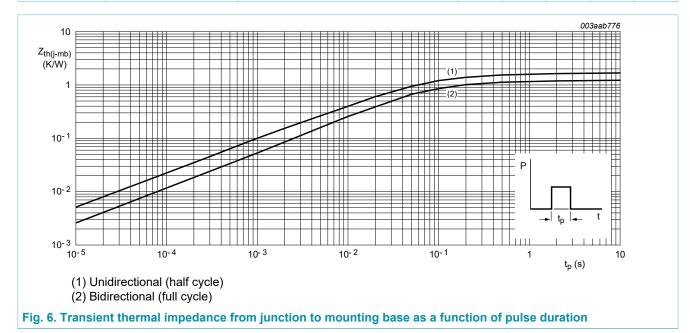


6 / 14

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; Fig. 6	-	-	1.2	K/W
	from junction to mounting base	half cycle; Fig. 6	-	-	1.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	2	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	2	-	10	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	30	mA
	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	30	mA	
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.8	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 ^{\circ}\text{C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 150 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics		·			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	20	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	0.8	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 10 V/µs; gate open circuit	1.2	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 1 V/µs; gate open circuit	6	-	-	A/ms

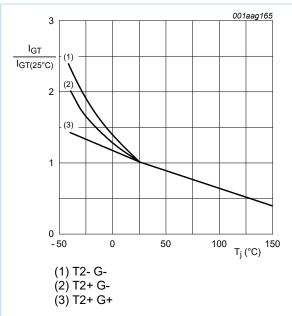


Fig. 7. Normalized gate trigger current as a function of junction temperature

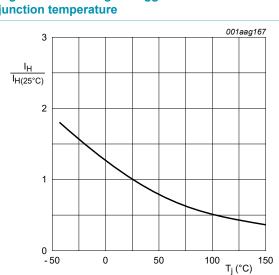


Fig. 9. Normalized holding current as a function of junction temperature

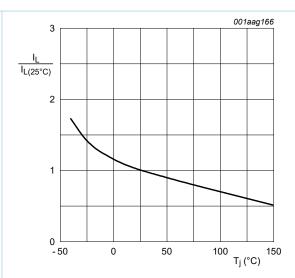
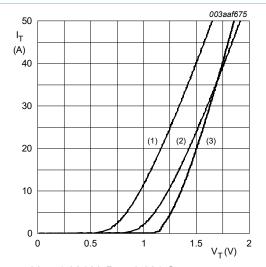


Fig. 8. Normalized latching current as a function of junction temperature



 $V_o = 1.024 \text{ V}; R_s = 0.021 \Omega$

(1) T_i = 150 °C; typical values

(2) T_j = 150 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

9 / 14

WeEn Semiconductors BTA316-600ET

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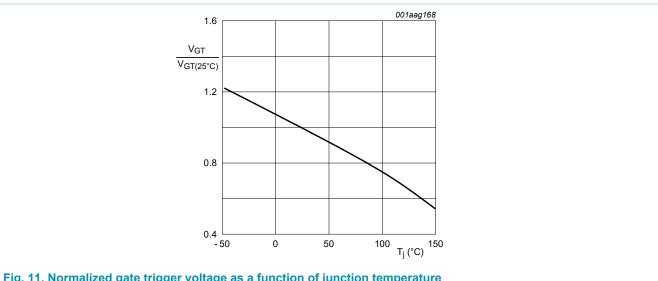
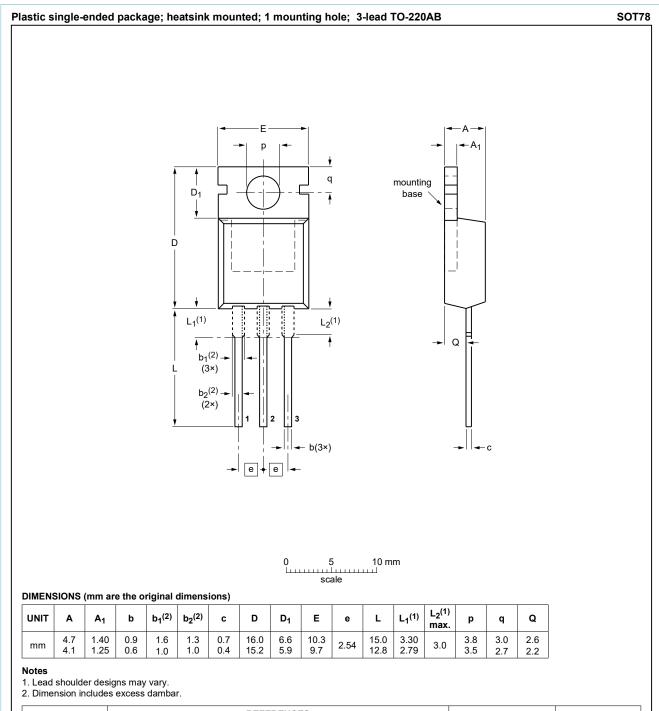


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline



	EUROPEAN	ISSUE DATE
VERSION IEC JEDEC JEITA	PROJECTION	ISSUE DATE
SOT78 3-lead TO-220AB SC-46		08-04-23 08-06-13

Fig. 12. Package outline TO-220AB (SOT78)

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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13 / 14

13. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	3
8.	Limiting values	4
9.	Thermal characteristics	7
10	. Characteristics	8
11	. Package outline	11
12	Legal information	12

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